

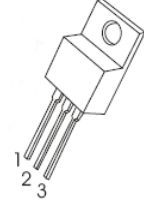
2SB1375 TRANSISTOR (PNP)

FEATURES

- High Power Dissipation: $P_C=25W(T_C=25^\circ C)$
- Low voltage: $V_{CE(sat)}=-1.5V(Max)(I_C=-2A, I_B=-0.2A)$
- Collector Metal(Fin)is Coverd with Mold Resin
- Complementary to 2SD2012

TO-220-3L

1. BASE
2. COLLECTOR
3. EMITTER

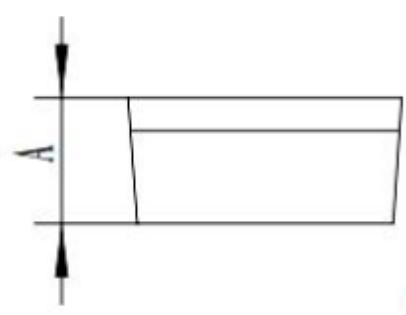
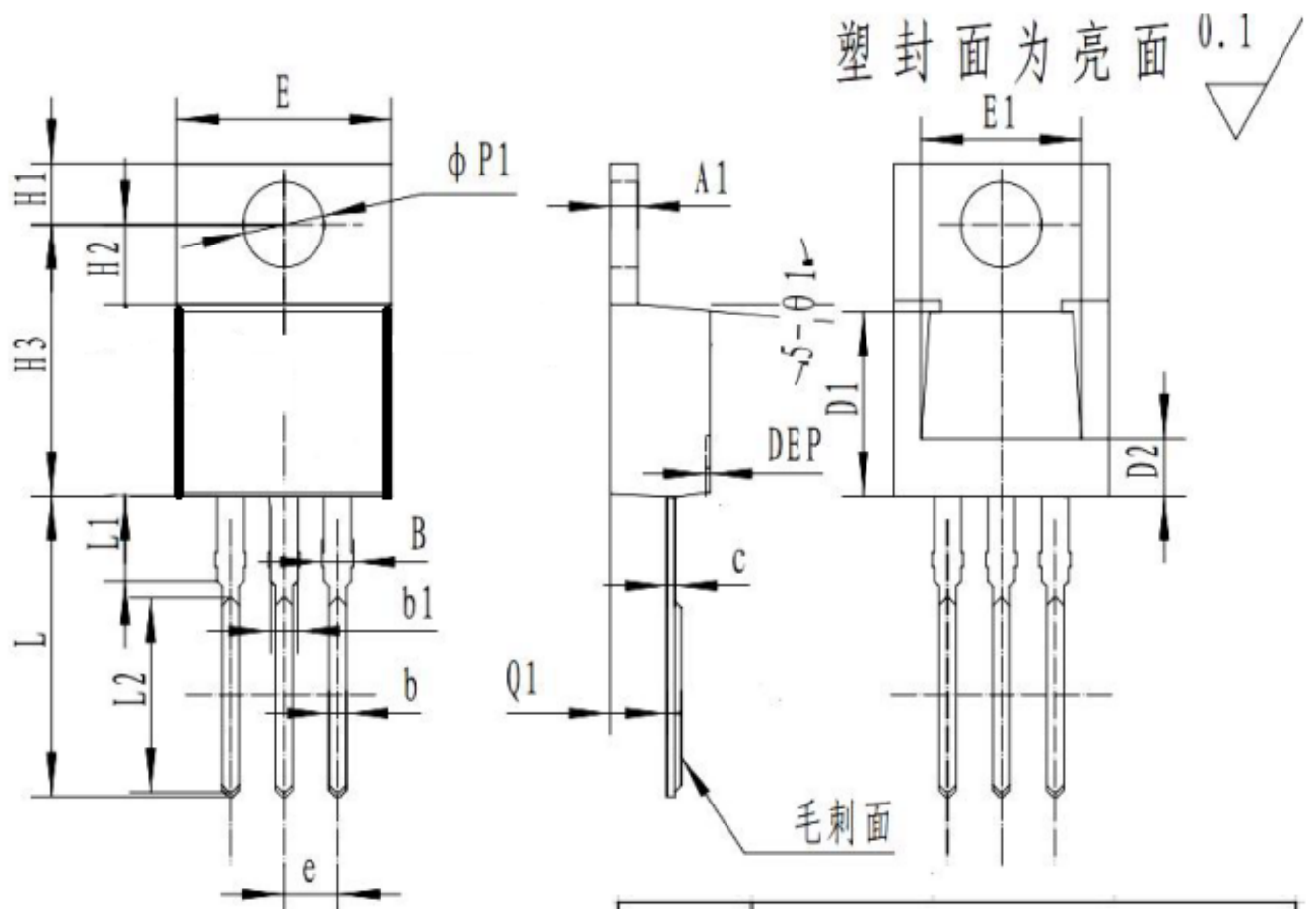


MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Dissipation	2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7V, I_C=0$			-10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-0.5A$	100		320	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-2A$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V, I_C=-0.5A$			-1	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.5A$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		50		pF



SYMBOL	MM		
	MIN	NOM	MAX
*A	4.60	4.70	4.80
A1	1.22	1.27	1.32
*b	0.76	0.81	0.86
b1	1.22	1.27	1.32
*B	1.27	1.37	1.45
*c	0.33	0.38	0.43
D1	7.60	7.75	7.90
D2	2.50	2.60	2.70
*E	10.00	10.10	10.20
E1	7.70	7.80	7.90
H1	2.64	2.74	2.84
H2	3.46	3.56	3.66
*H3	12.10	12.20	12.30
H4	1.90	2.00	2.10
*e	2.49	2.54	2.59
*L	13.45	3.85	13.85
L1	3.58	3.78	3.98
L2	8.66	8.76	8.86
*Q1	2.59	2.69	2.79
$\theta 1$	3°	5°	7°
$\phi P1$	3.85	3.90	3.95
DEP	0.05	0.10	0.20

带*为检验尺寸